NTMFS4119N

Power MOSFET

30 V, 30 A, Single N−Channel, SO−8 Flat Lead

Features

- Low $R_{DS(on)}$
- Fast Switching Times
- Low Inductance SO−8 Package
- These are Pb−Free Devices

Applications

- Notebooks, Graphics Cards
- Low Side Switch
- DC−DC

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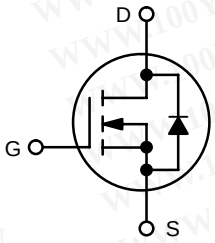
$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max (Note 1)
30 V	2.3 mΩ @ 10 V	30 A
	3.1 mΩ @ 4.5 V	



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

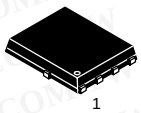
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	18	A
		T_A = 85°C		13	
	t ≤ 10 s	T_A = 25°C		30	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	2.3	W
	t ≤ 10 s			6.1	
Continuous Drain Current (Note 2)	Steady State	T_A = 25°C	I_D	11	A
		T_A = 85°C		8.0	
Power Dissipation (Note 2)		T_A = 25°C	P_D	0.9	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	89	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 150	°C
Source Current (Body Diode)			I_S	8.0	A
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 30 V, V_{GS} = 10 V, I_{PK} = 29 A, L = 1 mH, R_G = 25 Ω)			E_{AS}	421	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State	$R_{\theta JC}$	1.3	°C/W
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	53.7	
Junction−to−Ambient − t ≤ 10 s (Note 1)	$R_{\theta JA}$	20.5	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	138.5	

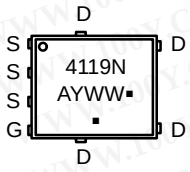
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface mounted on FR4 board using the minimum recommended pad size (Cu area = 0.412 in sq).



SO−8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



4119N = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4119NT1G	SO−8 FL (Pb−Free)	1500 Tape & Reel
NTMFS4119NT3G	SO−8 FL (Pb−Free)	5000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				19		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.0		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				7.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 29 A			2.3	3.5	mΩ
		V_{GS} = 4.5 V, I_D = 25 A			3.1	4.8	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 10 A			23		S
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 24 V			4800		pF
Output Capacitance	C_{OSS}				800		
Reverse Transfer Capacitance	C_{RSS}				530		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 18 A			36.8	60	nC
Threshold Gate Charge	$Q_{G(TH)}$				7.3		
Gate−to−Source Charge	Q_{GS}				11		
Gate−to−Drain Charge	Q_{GD}				17.4		
Gate Resistance	R_G				0.73		Ω
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 1.0 A, R_G = 3.0 Ω			28		ns
Rise Time	t_r				26		
Turn−Off Delay Time	$t_{d(OFF)}$				35		
Fall Time	t_f				40		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 8.0 A	T_J = 25°C		0.74	1.0	V
			T_J = 125°C		0.56		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 8.0 A			36.5		ns
Charge Time	t_a				19.3		
Discharge Time	t_b				19.8		
Reverse Recovery Charge	Q_{RR}				37		nC

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

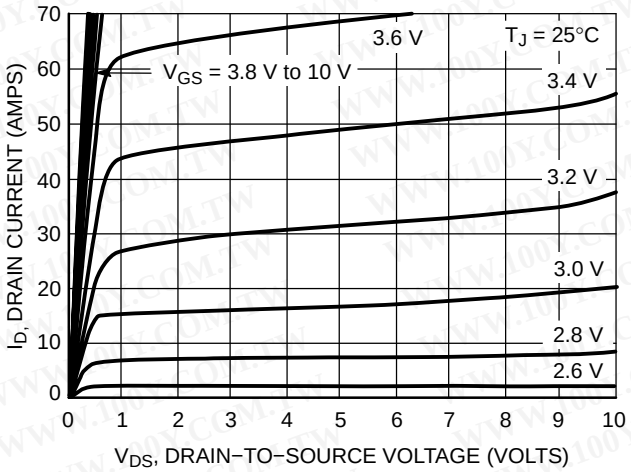


Figure 1. On−Region Characteristics

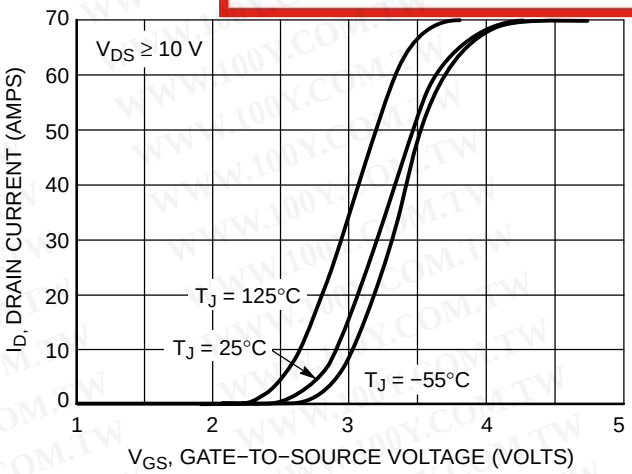


Figure 2. Transfer Characteristics

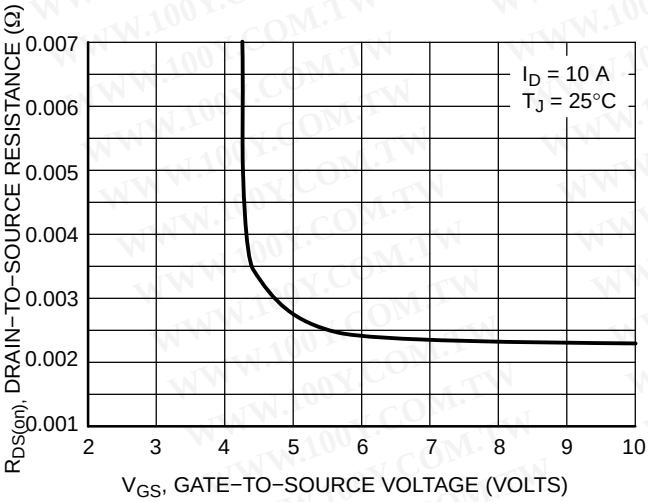


Figure 3. On−Resistance vs. Gate−to−Source Voltage

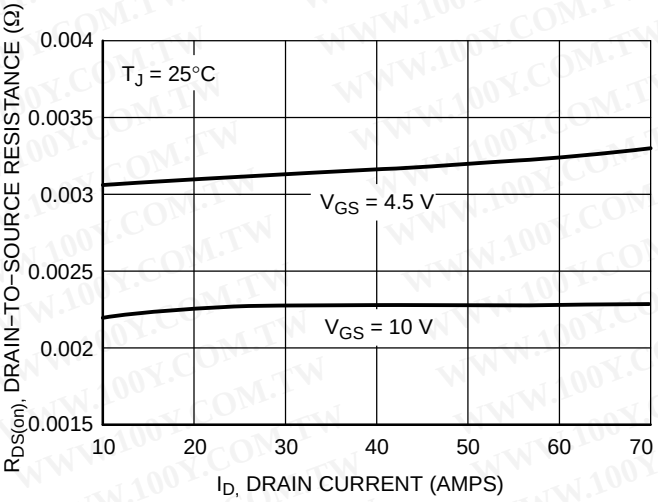


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

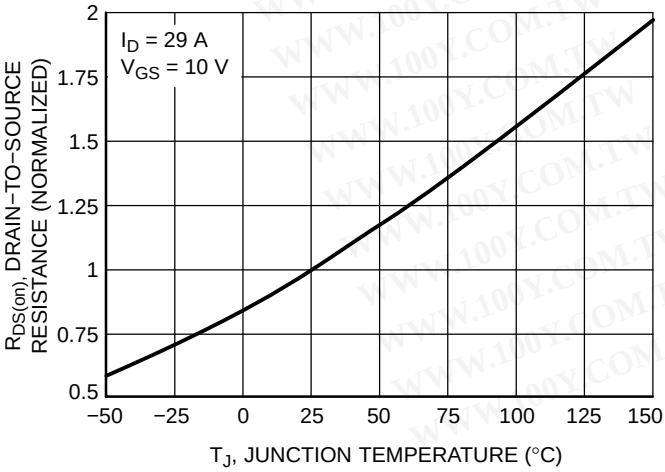


Figure 5. On−Resistance Variation with Temperature

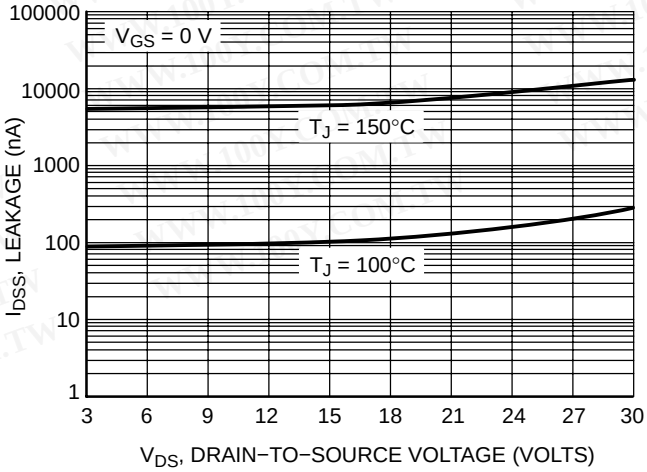


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

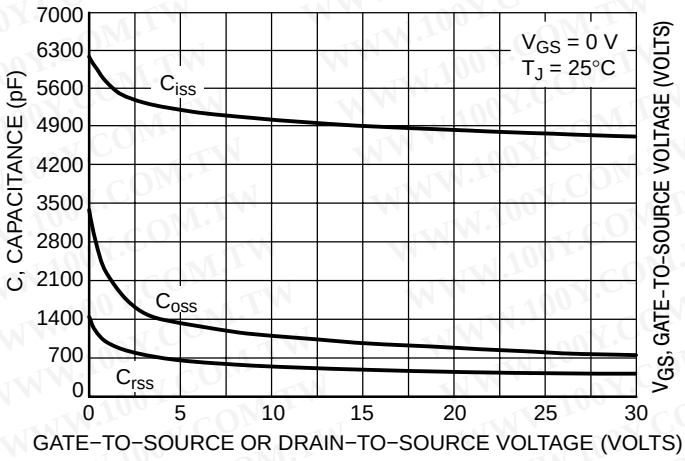


Figure 7. Capacitance Variation

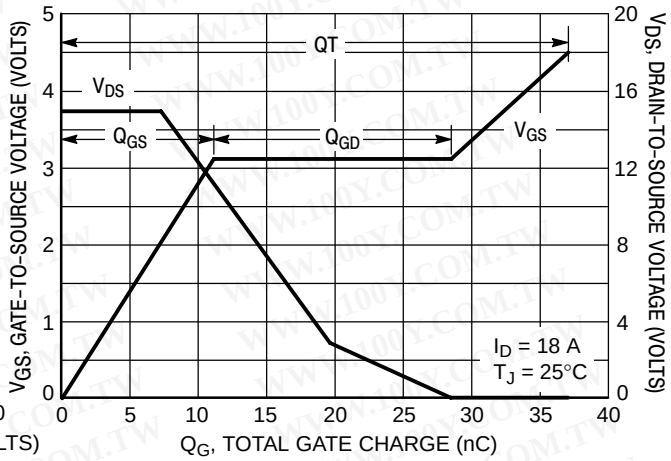


Figure 8. Gate−To−Source and Drain−To−Source Voltage vs. Total Charge

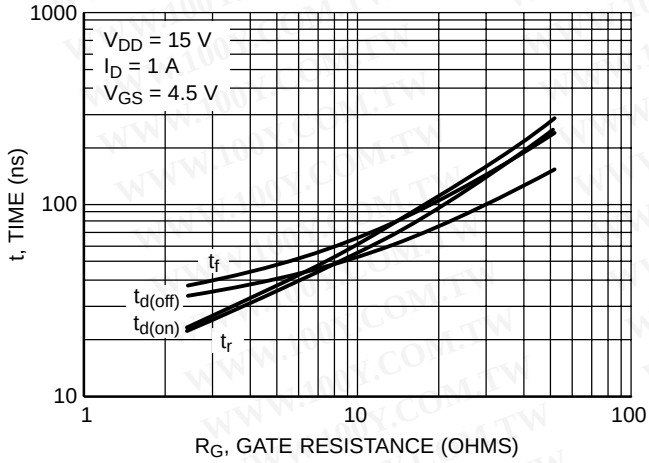


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

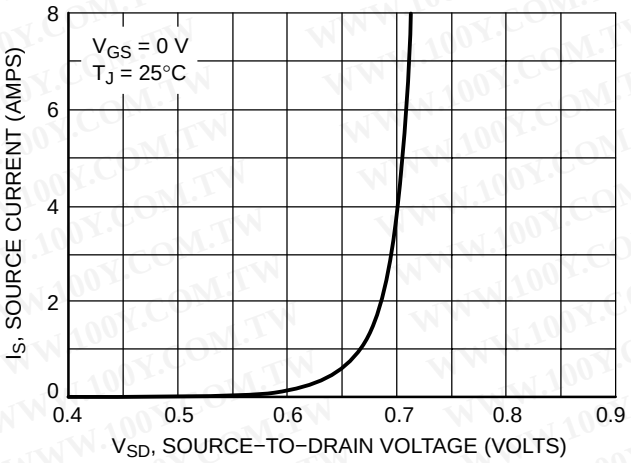
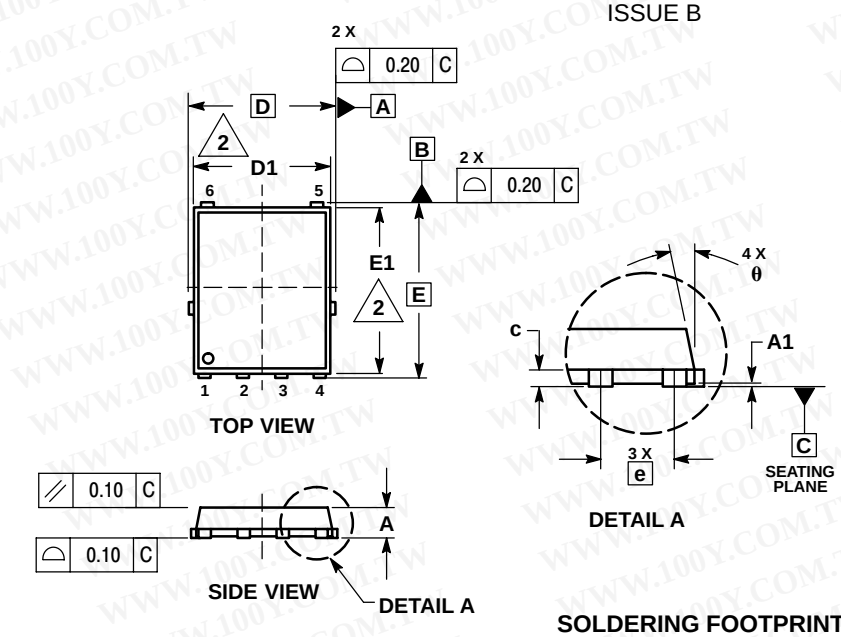


Figure 10. Diode Forward Voltage vs. Current

NTMFS4119N

PACKAGE DIMENSIONS

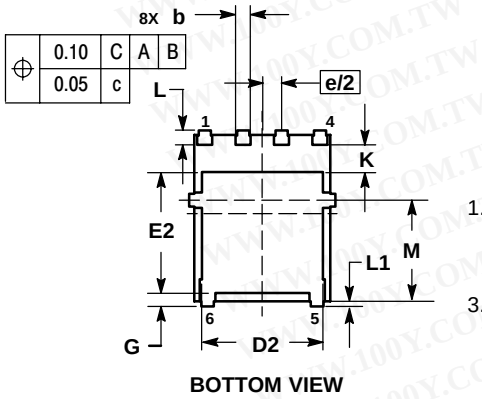
DFN6 5*6*1 1.27 PITCH
(SO8 FL)
CASE 488AA−01
ISSUE B



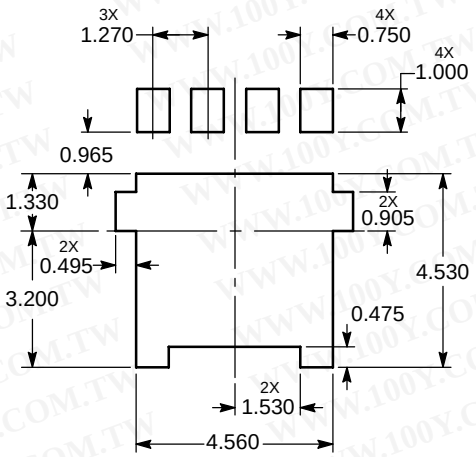
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	0.99	1.20
A1	0.00	−−−	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D		5.15 BSC	
D1	4.50	4.90	5.10
D2	3.50	−−−	4.22
E		6.15 BSC	
E1	5.50	5.80	6.10
E2	3.45	−−−	4.30
e		1.27 BSC	
G	0.51	0.61	0.71
K	0.51	−−−	−−−
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °	−−−	12 °

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN



SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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